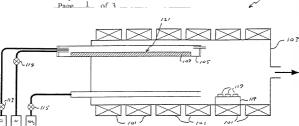
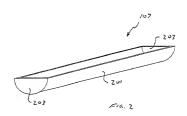
In re. application of Yuri V. Melnik, et al. Express Mail No. EL828015470US
Atty. David G. Beck (415) 393-2404
Atty. Docket No. 23600-700



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